



# DCR780G42

# **Phase Control Thyristor**

DS5829-5 February 2014 (LN31341)

## **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR780G42 DCR780G40 DCR780G38	4200 4000 3800	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 100\text{mA}, \\ V_{DRM}, V_{RRM}  t_p = 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} = \\ V_{DRM}  \&  V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available.

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR780G42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

## **KEY PARAMETERS**

$V_{DRM}$	4200V
$I_{T(AV)}$	780A
I <sub>TSM</sub>	10500A
dV/dt*	1500V/µs
dl/dt	400A/us

# \* Higher dV/dt selections available

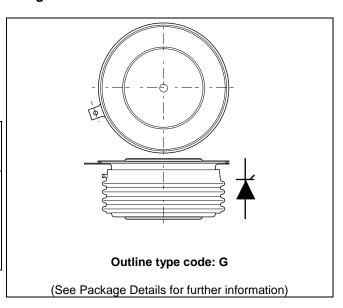


Fig. 1 Package outline



# **CURRENT RATINGS**

# $T_{case} = 60$ °C unless stated otherwise

Symbol Parameter		Test Conditions	Max.	Units
Double Sid	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	780	А
I <sub>T(RMS)</sub>	RMS value	-	1225	А
I <sub>T</sub>	Continuous (direct) on-state current	-	1173	Α

# **SURGE RATINGS**

Symbol Parameter		Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	10.5	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	0.55	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Test Conditions		Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0268	°C/W
		Single side cooled	Anode DC	-	0.0527	°C/W
			Cathode DC	-	0.0652	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 11.5kN	Double side	-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			10	13	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	ite open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	400	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
V <sub>T(TO)</sub>	Threshold voltage – Low level	100A to 500A at T <sub>case</sub> = 125°	С	-	.87	V
	Threshold voltage – High level	500A to 3000A at T <sub>case</sub> = 125°C		-	1.053	V
r <sub>T</sub>	On-state slope resistance – Low level	100A to 500A at T <sub>case</sub> = 125°C		-	1.2244	mΩ
	On-state slope resistance – High level	500A to 3000A at T <sub>case</sub> = 125°C		-	0.8443	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source	30V, 10Ω	TBD	TBD	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 100$	= 5A/μs,	300	600	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt = 5A/\mu s$ ,		1100	2200	μC
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I <sub>T</sub> = 5A	-	300	mA



## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

### **CURVES**

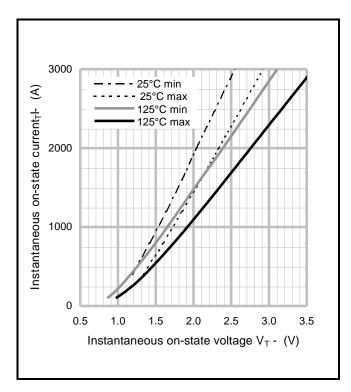


Fig.2 Maximum & minimum on-state characteristics

**V<sub>TM</sub> EQUATION** 

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.251561

B = 0.154175C = 0.000839

D = -0.007548

these values are valid for  $T_j = 125$ °C for  $I_T 50$ A to 3000A

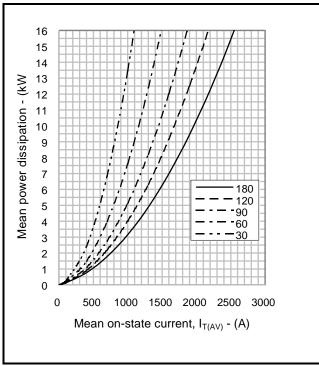


Fig.3 On-state power dissipation - sine wave

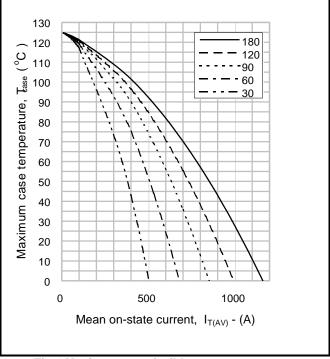


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

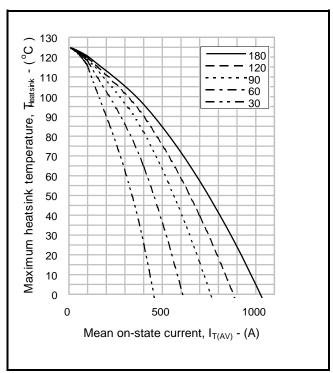


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

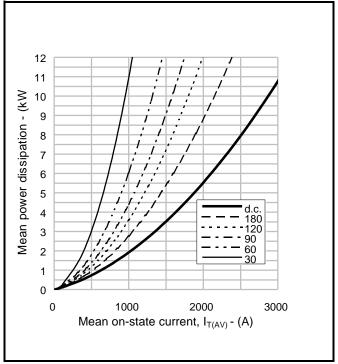


Fig.6 On-state power dissipation - rectangular wave

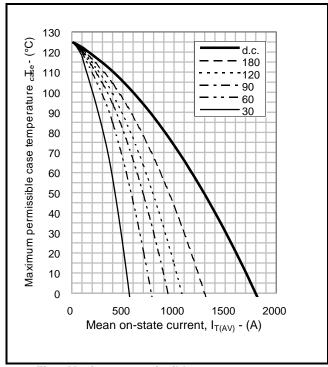


Fig.7 Maximum permissible case temperature, double side cooled - rectangular wave

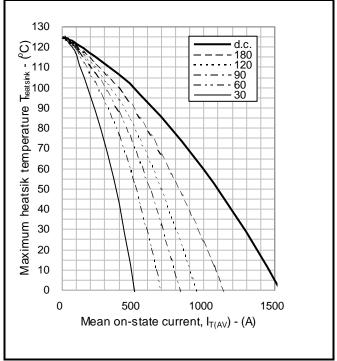
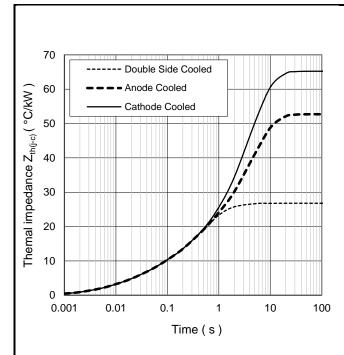


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	2.2995	5.4226	16.9074	2.1488
	T <sub>i</sub> (s)	0.0066401	0.0457025	0.4962482	1.8248
Anode side cooled	R <sub>i</sub> (°C/kW)	2.3214	5.2661	10.2686	34.8031
	T <sub>i</sub> (s)	0.0066948	0.045528	0.3484209	4.582
Cathode side cooled	R <sub>i</sub> (°C/kW)	2.4895	5.9105	7.4256	49.3432
l	T. (e)	0.0070404	0.053005	0.3033003	4 2205

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(-T/T_i))]$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

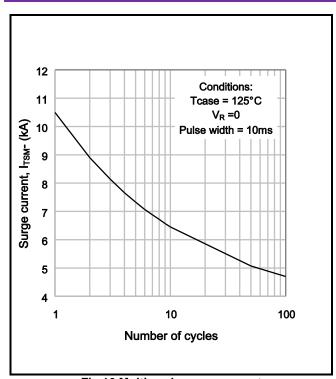
Tables show the increments of thermal resistance  $R_{\text{th}(j\cdot c)}$  when the device operates at conduction angles other than d.c.

Double side cooling					
	ΔZ <sub>th</sub> (	$\Delta Z_{th}(z)$			
θ°	sine.				
180	4.15	2.72			
120	4.90	4.02			
90	5.74	4.79			
60	6.53	5.65			
30	7.16	6.64			

	Double side co	oling		Anode Side	Cooling	1	Ca	t
	$\Delta Z_{th}$ (	(z)		$\Delta Z$	th (z)			
θ°	sine.	rect.	θ°	sine.	rect.		θ°	
180	4.15	2.72	180	4.15	2.72		180	
120	4.90	4.02	120	4.89	4.02		120	
90	5.74	4.79	90	5.73	4.78		90	
60	6.53	5.65	60	6.52	5.65		60	
30	7.16	6.64	30	7.15	6.62	I	30	
15	7.46	7.18	15	7.44	7.16		15	

Ca	Cathode Sided Cooling					
	$\Delta Z_{th}(z)$					
θ°	sine.	rect.				
180	4.13	2.71				
120	4.87	4.00				
90	5.69	4.76				
60	6.46	5.60				
30	7.07	6.56				
4.5		7.00				

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)



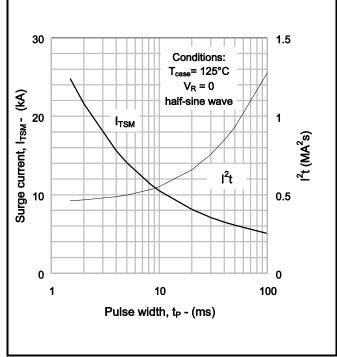
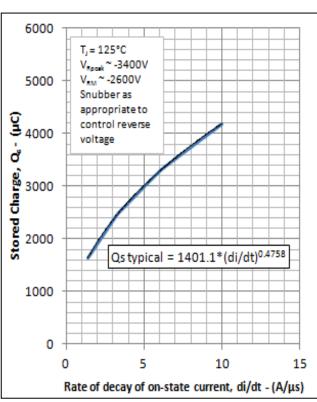
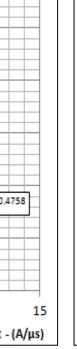


Fig.10 Multi-cycle surge current

Fig.11 Single-cycle surge current





180

160

7 Current, 187- (µC)

80

60

40

20

Reverse Recovery

T<sub>1</sub> = 125°C Vpeak = -3400V

Snubber as

voltage

Vline = -2600V

appropriate to

control reverse

Fig.12 Stored Charge vs di/dt

Irr typical = 32.209\*(di/dt)0.6973

15

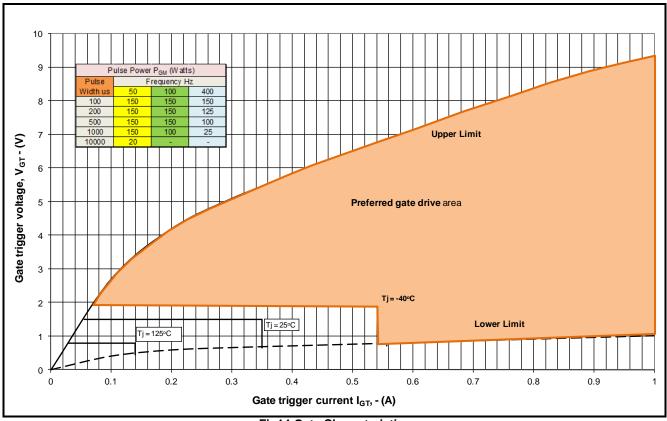


Fig14 Gate Characteristics

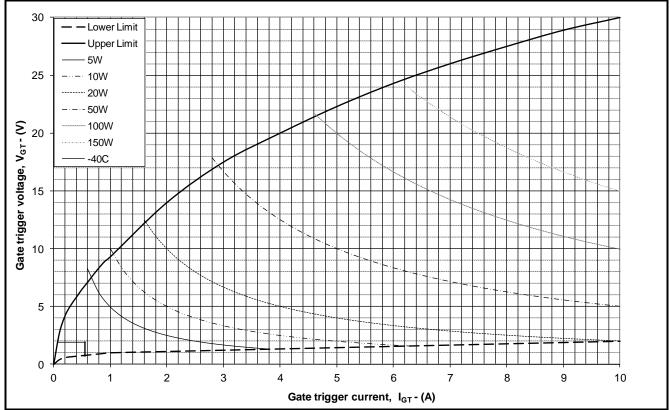


Fig. 15 Gate characteristics





### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

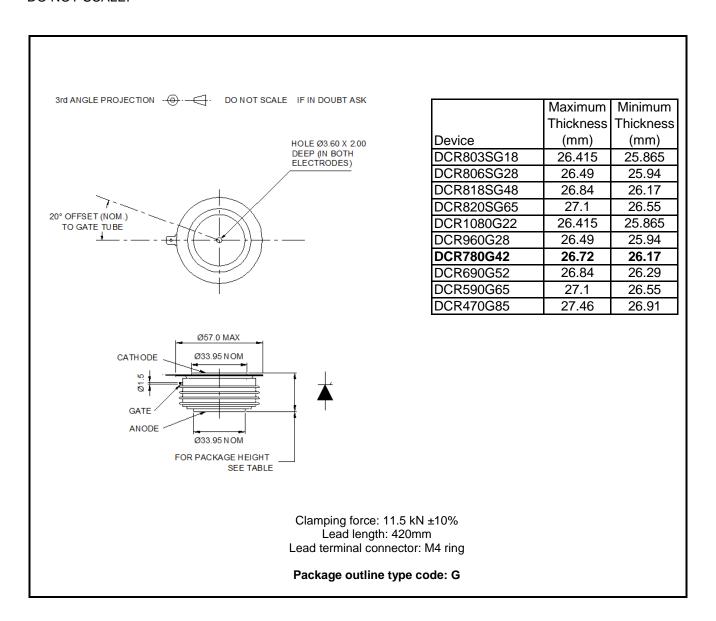


Fig.16 Package outline





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No actual design work on the product has been started.

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